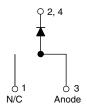


HEXFRED® Ultrafast Soft Recovery Diode, 4 A





PRODUCT SUMMARY					
Package D-PAK (TO-252AA)					
I _{F(AV)}	4 A				
V_R	600 V				
V _F at I _F	1.8 V				
t _{rr} typ.	17 ns				
T _J max.	150 °C				
Diode variation	Single die				

FEATURES

- Ultrafast recovery time
- Ultrasoft recovery
- Very low I_{RRM}
- Very low Q_{rr}
- · Guaranteed avalanche
- Specified at operating temperature
- Compliant to RoHS Directive 2002/95/EC
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C

BENEFITS

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- · Higher frequency operation
- · Reduced snubbing
- · Reduced parts count

DESCRIPTION/APPLICATIONS

These diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems. The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for freewheeling, flyback, power converters, motor drives, and other applications where high speed and reduced switching losses are design requirements.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Cathode to anode voltage	V_{RRM}		600	V			
Maximum continuous forward current	I _{F(AV)}	T _C = 100 °C	4				
Single pulse forward current	I _{FSM}		25	Α			
Repetitive peak forward current	I _{FRM}	T _C = 116 °C	16				
Maximum power dissipation	P_D	T _C = 100 °C	10	W			
Operating junction and storage temperatures	T _J , T _{Stg}		- 55 to 150	°C			

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V _{BR} , V _R	Ι _R = 100 μΑ	600	-	-	
Forward voltage See fig. 1	V _F	I _F = 4 A	-	1.5	1.8	V
		I _F = 8 A	-	1.8	2.2	
		I _F = 4 A, T _J = 125 °C	-	1.4	1.7	
Maximum reverse I _R		$V_R = V_R$ rated	-	0.17	3.0	
		$T_J = 125 ^{\circ}\text{C}, V_R = 0.8 \text{x} \text{V}_R \text{rated}$	-	44	300	μΑ
Junction capacitance	C _T	V _R = 200 V	-	4	8	pF
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH

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DYNAMIC RECOVERY CHARACTERISTICS (T _C = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS	
		I _F = 1.0 A, dI _F /dt = 200 A/μA, V _R = 30 V		-	17	-		
Reverse recovery time	t _{rr}	T _J = 25 °C		-	28	42	ns	
		T _J = 125 °C		-	38	57		
Peak recovery current	I _{RRM}	T _J = 25 °C		-	2.9	5.2	۸	
		IRRM	T _J = 125 °C	$I_F = 4 \text{ A}$	-	3.7	6.7	А
Dougrap rapovani chargo	0	T _J = 25 °C	dl _F /dt = 200 A/μs V _R = 200 V	-	40	60	nC	
Reverse recovery charge	Q_{rr} $T_J = 125 °C$	T _J = 125 °C		-	70	105	IIC IIC	
Rate of fall of recovery current	dl _{(rec)M} /dt	att /att	T _J = 25 °C		-	280	-	Λ/μο
		T _J = 125 °C		-	235	-	A/μs	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		- 55	-	150	°C
Thermal resistance, junction to case	R _{thJC}		-	-	5.0	°C/W
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	- C/VV
Weight			-	2.0	-	g
vveignt			-	0.07	-	OZ.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking device		Case style D-PAK		HFA04	SD60S	•

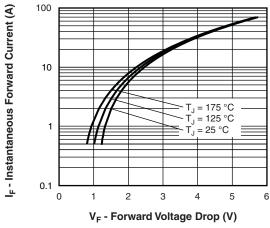


Fig. 1 - Typical Forward Voltage Drop Characteristics

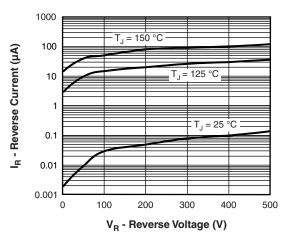


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

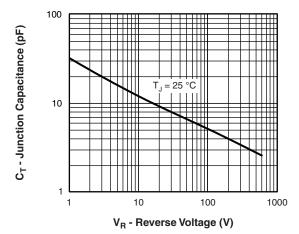


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

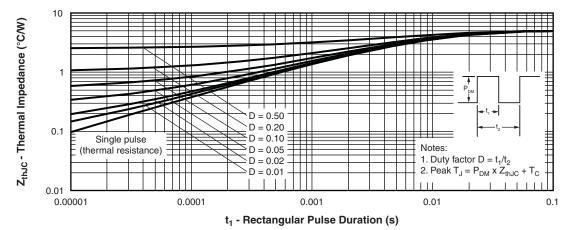


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics





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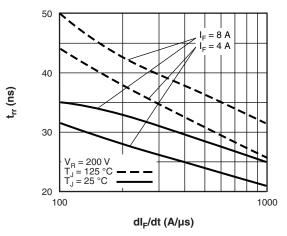


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

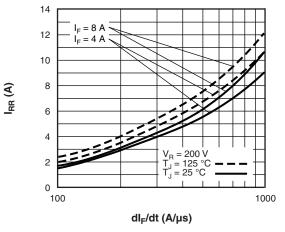


Fig. 6 - Typical Recovery Current vs. dl_F/dt

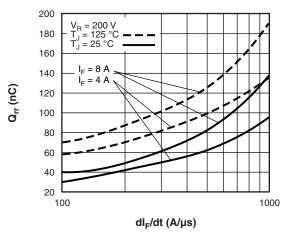


Fig. 7 - Typical Stored Charge vs. dl_F/dt

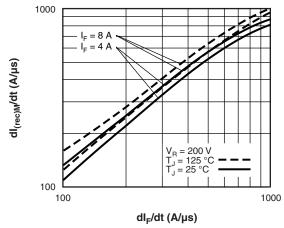


Fig. 8 - Typical dl_{(rec)M}/dt vs. dl_F/dt

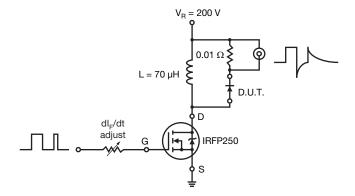
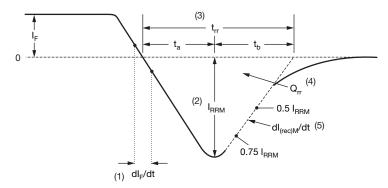


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dI_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_{r}$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

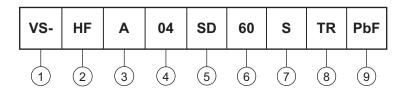
(5) dl_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions



ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - HEXFRED® family

3 - Electron irradiated

- Current rating (04 = 4 A)

5 - D-PAK

Voltage rating (60 = 600 V)

7 - S = D-PAK

8 - • TR = Tape and reel

• TRR = Tape and reel (right oriented)

• TRL = Tape and reel (left oriented)

9 - • PbF = Lead (Pb)-free

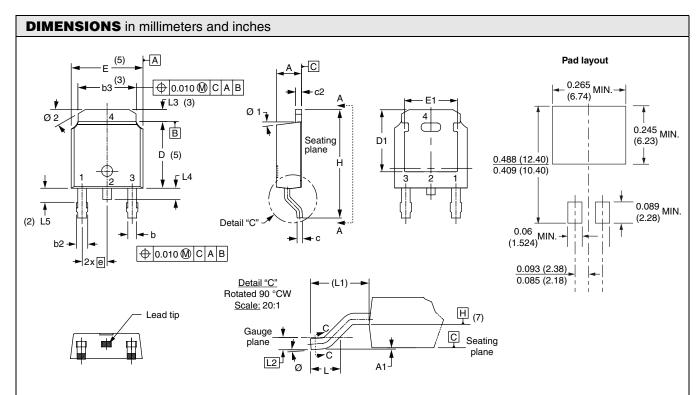
• P = Lead (Pb)-free (for TRR and TRL)

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95016				
Part marking information	www.vishay.com/doc?95059				
Packaging information	www.vishay.com/doc?95033				



Vishay High Power Products

D-PAK (TO-252AA)



SYMBOL	MILLIM	MILLIMETERS		INCHES	
STWIDOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	2.18	2.39	0.086	0.094	
A1	-	0.13	-	0.005	
b	0.64	0.89	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	3
С	0.46	0.61	0.018	0.024	
c2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	5
D1	5.21	-	0.205	1	3
Е	6.35	6.73	0.250	0.265	5
E1	4.32	-	0.170	-	3

SYMBOL	MILLIM	ETERS	INCHES		NOTES
STWBOL	MIN.	MAX.	MIN.	MAX.	NOTES
е	2.29	BSC	0.090	BSC	
Н	9.40	10.41	0.370	0.410	
L	1.40	1.78	0.055	0.070	
L1	2.74 BSC		0.108 REF.		
L2	0.51 BSC		0.020 BSC		
L3	0.89	1.27	0.035	0.050	3
L4	-	1.02	-	0.040	
L5	1.14	1.52	0.045	0.060	2
Ø	0°	10°	0°	10°	
Ø1	0°	15°	0°	15°	
Ø2	25°	35°	25°	35°	

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension uncontrolled in L5
- (3) Dimension D1, E1, L3 and b3 establish a minimum mounting surface for thermal pad
- (4) Section C C dimension apply to the flat section of the lead between 0.13 and 0.25 mm (0.005 and 0.10") from the lead tip
- (5) Dimension D, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (6) Dimension b1 and c1 applied to base metal only
- $^{(7)}$ Datum A and B to be determined at datum plane H
- (8) Outline conforms to JEDEC outline TO-252AA





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